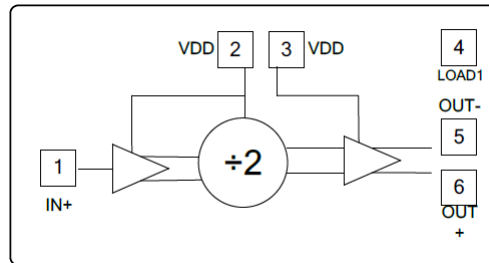


**Features**

- Frequency: 10-20GHz
- Output Power: -1dBm
- Single Power Supply: +5V/78mA
- DC blocking capacitor integrated on chip
- Die Size: 1.5 x 0.74 x 0.1 mm

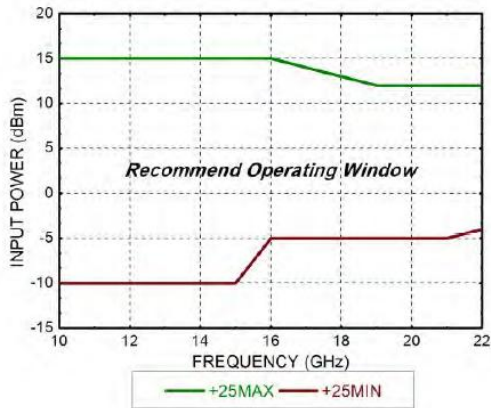
**Functional Block Diagram**

**Typical Applications**

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

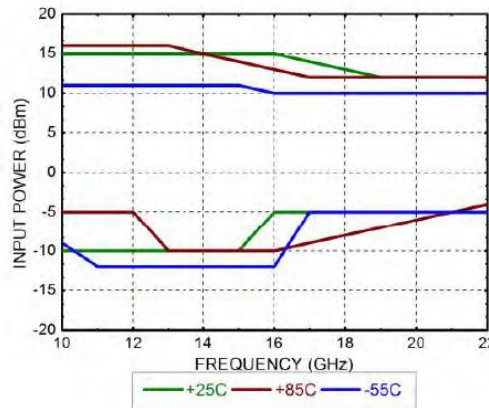
**Electrical Specifications**
**TA = +25°C, VDD = +5V, IDD=78mA**

Parameters	Condition	Min.	Typ.	Max.	Units
<b>Maximum Input Frequency</b>			<b>20</b>	<b>26</b>	<b>GHz</b>
<b>Minimum Input Frequency</b>			<b>10</b>		
<b>Input Power</b>	$f_{IN}=10-15GHz$	<b>-10</b>	<b>0</b>	<b>+15</b>	<b>dBm</b>
	$f_{IN}=15-22GHz$	<b>-5</b>	<b>3</b>	<b>+12</b>	<b>dBm</b>
<b>Output Power</b>	$f_{IN}=10-20GHz$	<b>-4</b>	<b>-1.5</b>		<b>dBm</b>
	$f_{IN}=20-22GHz$	<b>-6</b>	<b>-4</b>		<b>dBm</b>
<b>Single sideband phase noise @100kHz offset</b>	$P_{IN}=0dBm,$ $f_{IN}=14GHz$		<b>-145</b>		<b>dBc/Hz</b>
<b>Reverse Leakage</b>	<b>OUT+,OUT-, Terminated</b>		<b>50</b>		<b>dB</b>
<b>Operating Current (IDD)</b>			<b>78</b>		<b>mA</b>

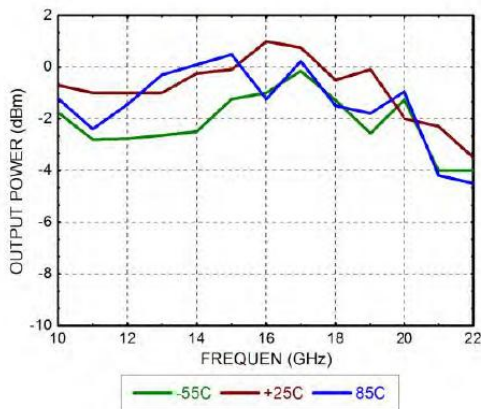
Input sensitivity window, T=25°C



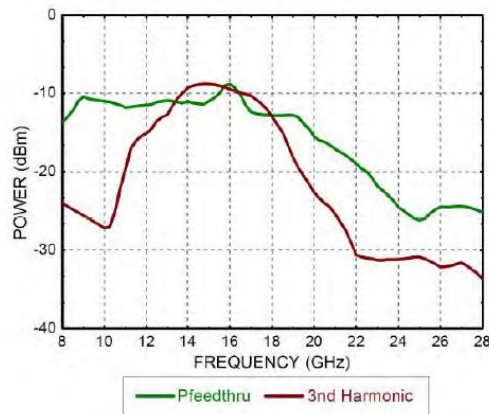
Input sensitivity window vs. Temperature



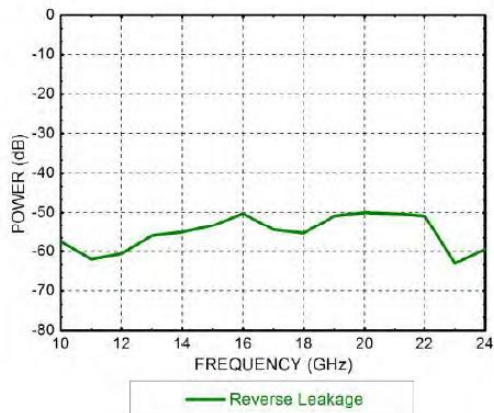
Output Power vs. Temperature



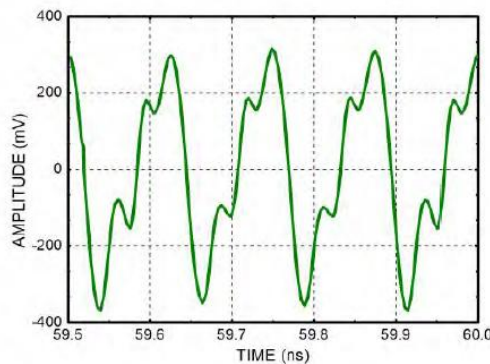
Output Harmonic, Pin=0dBm, T=25°C



Reverse Leakage, Pin=0dBm, T=25°C

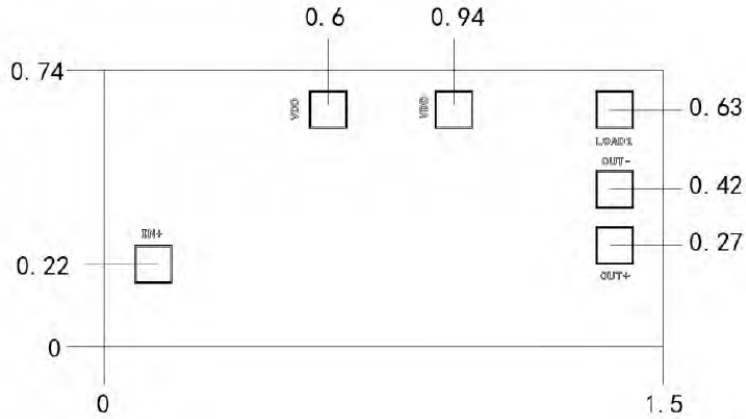


Output Waveform, Fout=8GHz, Pin=0dBm, T=25°C





**Outline Drawing:**  
All Dimensions in mm

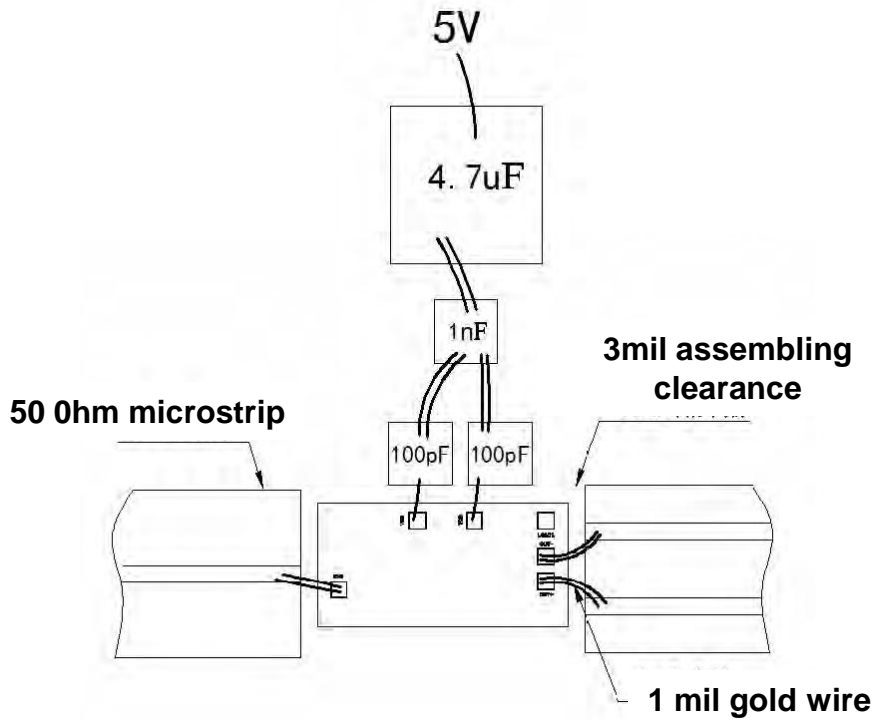


**Pad Description**

Pad	Function	Description
1	IN+	RF input, DC blocking capacitor integrated on chip
2,3	VDD	Power supply +5V, external 100pF/1nF/4.7uF bypass capacitor required.
4	LOAD1	Single-ended output configuration port, when Pad5 not used, connect it with Pad4
5	OUT-	Divided signal output, 180° phase difference with Pad6
6	OUT+	Divided signal output, DC blocking capacitor integrated on chip
Die bottom	GND	Die bottom must be connected to RF/DC ground.



### Assembly Drawing



•For single-ended output, connect Pad4 and Pad5 with gold bonding

#### Notes:

1. Die thickness: 100um
2. Typical bond pad is 100\*100  $\mu\text{m}^2$
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

#### Maximum Ratings:

1. Maximum drain voltage: +5.5V
2. Operating temperature: -55°C to +85°C
3. Storage temperature: -65°C to +150°C